

0.5-20GHz Driver GaAs Monolithic Microwave IC

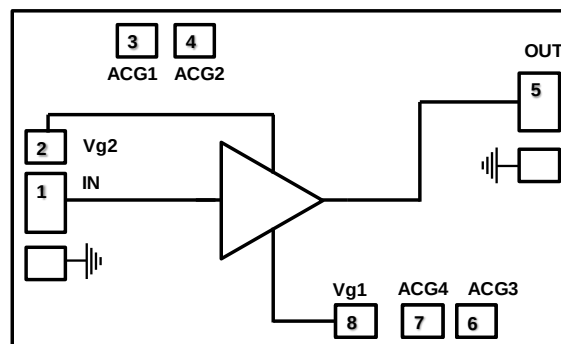
Description

The CHA4220-98F is a distributed driver amplifier which operates between 0.5 and 20GHz.

It is designed for a wide range of applications, such as military, telecom, test instrumentation.

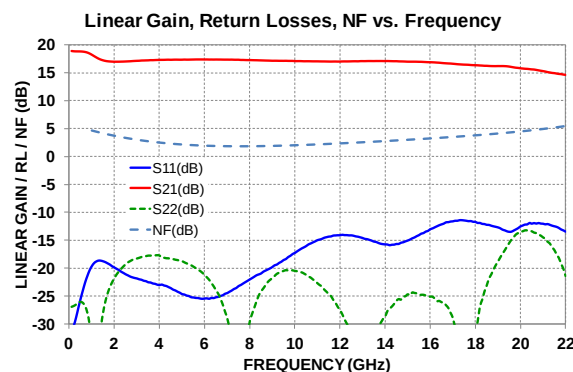
The circuit is manufactured with a pHEMT process, 0.25µm gate length, via holes through the substrate, air bridges and electron beam gate lithography.

It is supplied as bare die part with RF accesses matched on 50 ohms.



Main Features

- Broadband performances: 0.5-20GHz
- Typical Linear Gain: 17dB
- OP1dB: 20dBm
- Psat: 23dBm
- OIP3: 28dBm
- Typical Noise Figure: 3.5dB
- DC bias: Vd=7V@Id=120mA, Vg1#-0.2V and Vg2=1.5V.
- Bare die
- Die size: 3.04 x 1.56 x 0.1mm



Main Electrical Characteristics

Tamb.= +25°C

Symbol	Parameter	Min	Typ	Max	Unit
Freq	Frequency range	0.5		20	GHz
Gain	Linear Gain		17		dB
NF	Noise Figure		3.5		dB
Pout	Output Power @1dB comp.		20		dBm

Electrical Characteristics

Tamb.= +25°C, Vg1 to be set in order to have Idq=120mA, Vg2=1.5V

Symbol	Parameter	Min	Typ	Max	Unit
Freq	Frequency range	0.5		20	GHz
Gain	Linear Gain		17		dB
NF	Noise Figure		3.5		dB
IRL	Input Return Loss		15		dB
ORL	Output Return Loss		18		dB
P1dB	Output power for 1dB Compression For Freq=2-20 GHz		20		dBm
Psat	Saturated output power For Freq=2-20 GHz		23		dBm
OIP3	Output Third Order Intercept For Freq=2-20 GHz		28		dBm
Idq	Quiescent current on Vd		120		mA
Vd	Supply voltage on Vd	6	6.5	7	V
Id	Drain current @3dB gain compression		140		mA
Pin_max	Maximum input power For Vd=6V For Vd=7V		17		dBm
			15		dBm

The values are representative of typical "test fixture" measurements as defined on the drawing in paragraph "Evaluation test fixture".

Typical Bias Conditions

Tamb.= +25°C

Symbol	Pad N°	Parameter	Values	Unit
Vg1	8	Gate control1 for the amplifier	-0.2/-0.4	V
Vg2	2	Gate control2 for the amplifier	1.5	V
Vd	5	Drain Voltage	7	V

The associated drain current with no RF input power is Idq=120mA

This typical bias is recommended in order to get the best compromise between output power, linearity and Noise Figure performance vs. Temperature.

Absolute Maximum Ratings ⁽¹⁾T_{amb.}= +25°C

Symbol	Parameter	Values	Unit
V _d	Drain bias voltage	8V	V
I _{dq}	Drain bias current	170	mA
V _{g1}	Gate bias voltage V _{g1}	-2 to 0	V
V _{g2}	Gate bias voltage V _{g2}	1 to 2	V
P _{in}	Maximum peak input power overdrive	17	dBm
T _a	Operating temperature range (chip backside)	-40 to 85	°C
T _{stg}	Storage temperature range	-55 to +150	°C

⁽¹⁾ Operation of this device above anyone of these parameters may cause permanent damage: these maximum ratings parameters could not be cumulated.

These are stress ratings only, and functional operation of the device at these conditions is not implied.

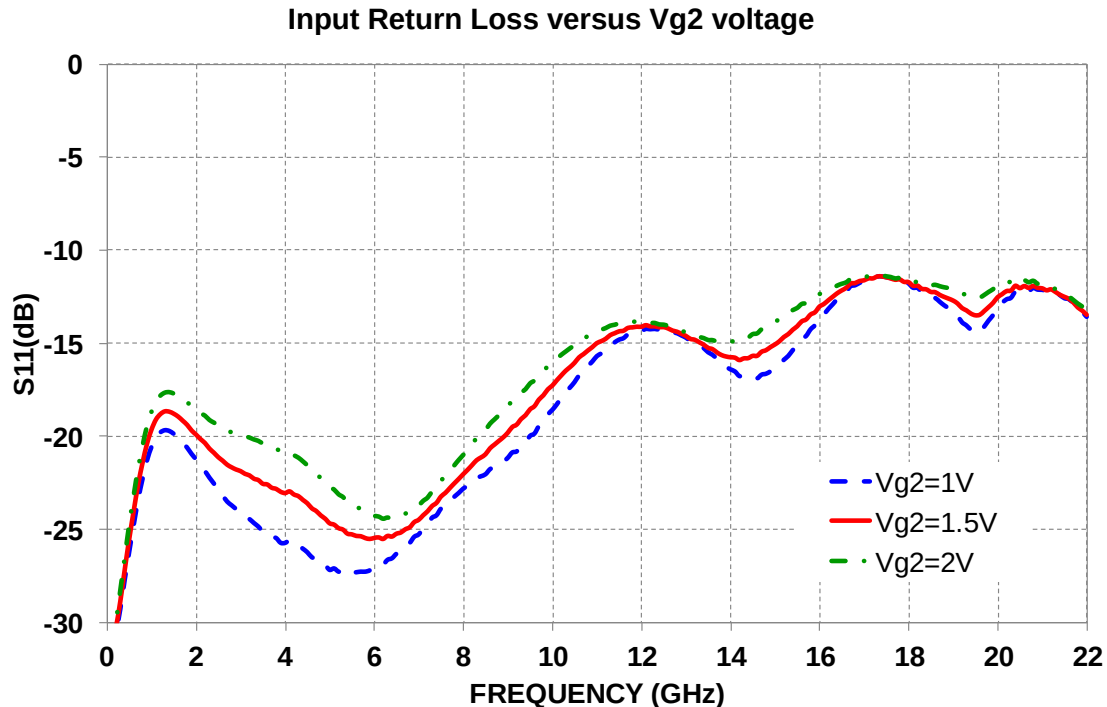
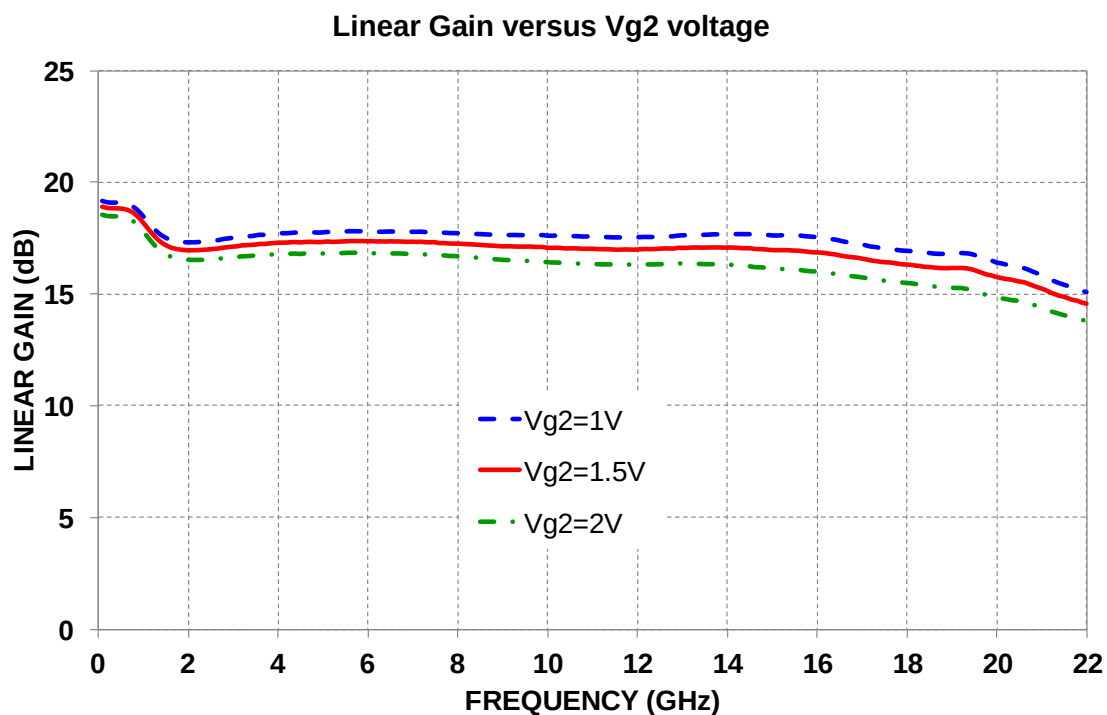
Maximum Junction temperature=175°C with T_a=+85°C.

R_{th_equivalent} =72°C/W → chip's equivalent thermal resistance from channel to die bottom with T_a. = +85°C and 7V & I_{dq}=120mA.

The R_{th_equivalent} is extrapolated, taking into account the full DC power and the channel temperature increase on the worst transistor.

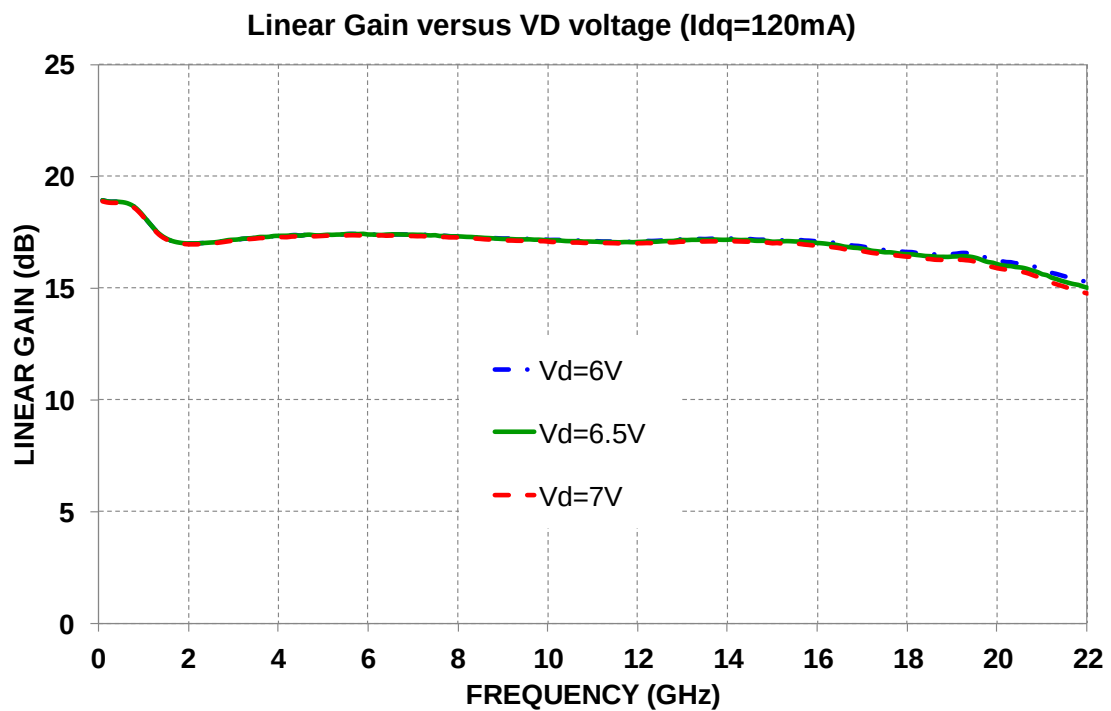
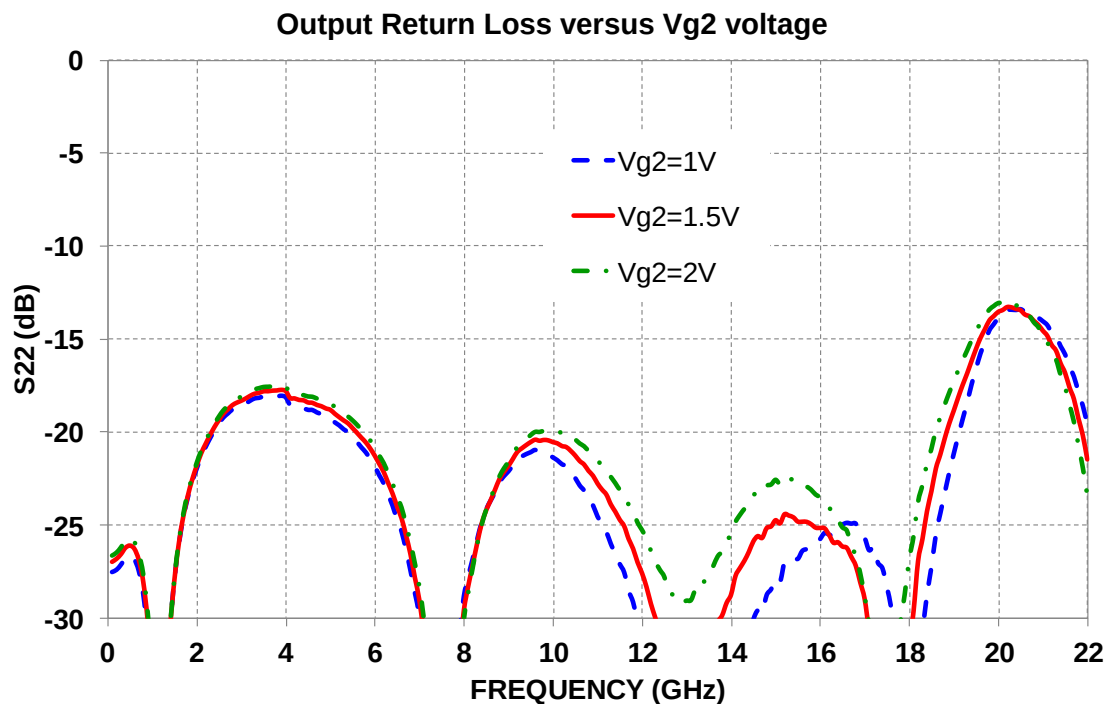
Typical Jig Measurements

Tamb.= +25°C, Vd=7V, Vg1 set in order to get Idq =120mA



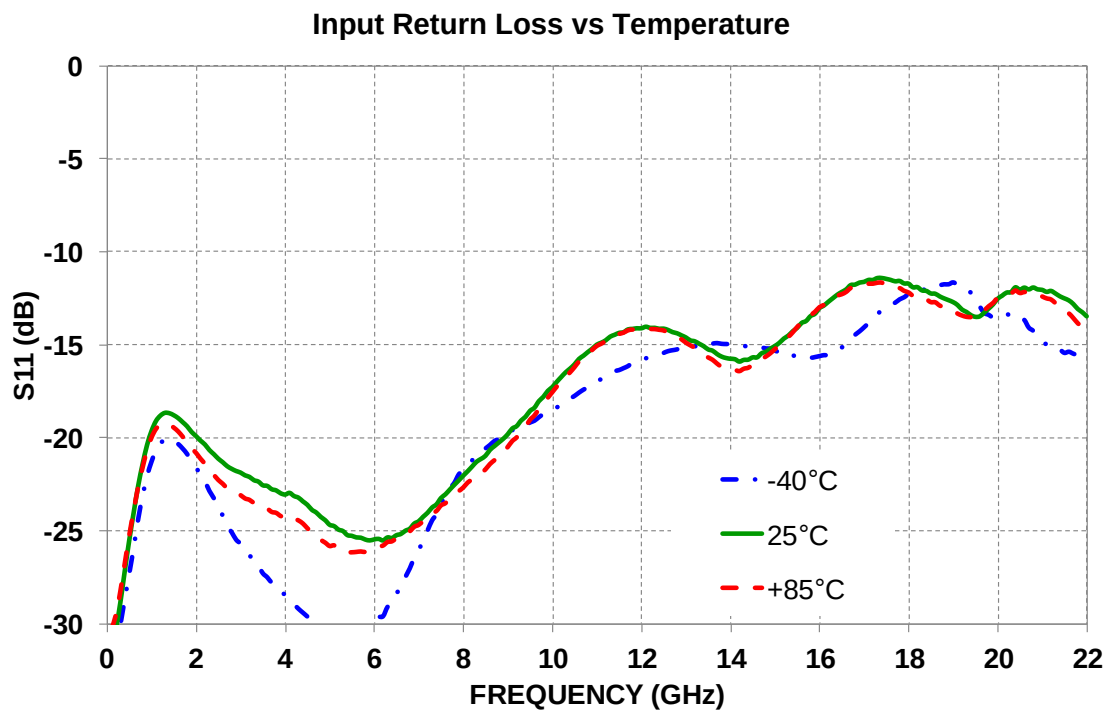
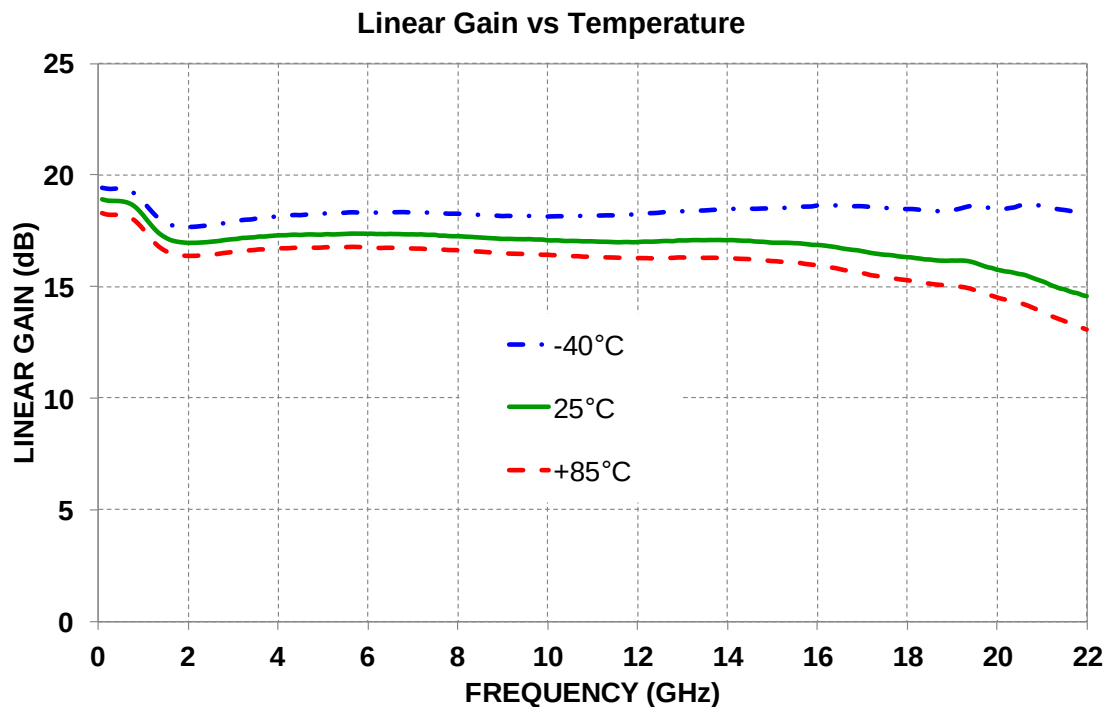
Typical Jig Measurements

Tamb.= +25°C, Vd =7V, Vg1 set in order to get Idq =120mA



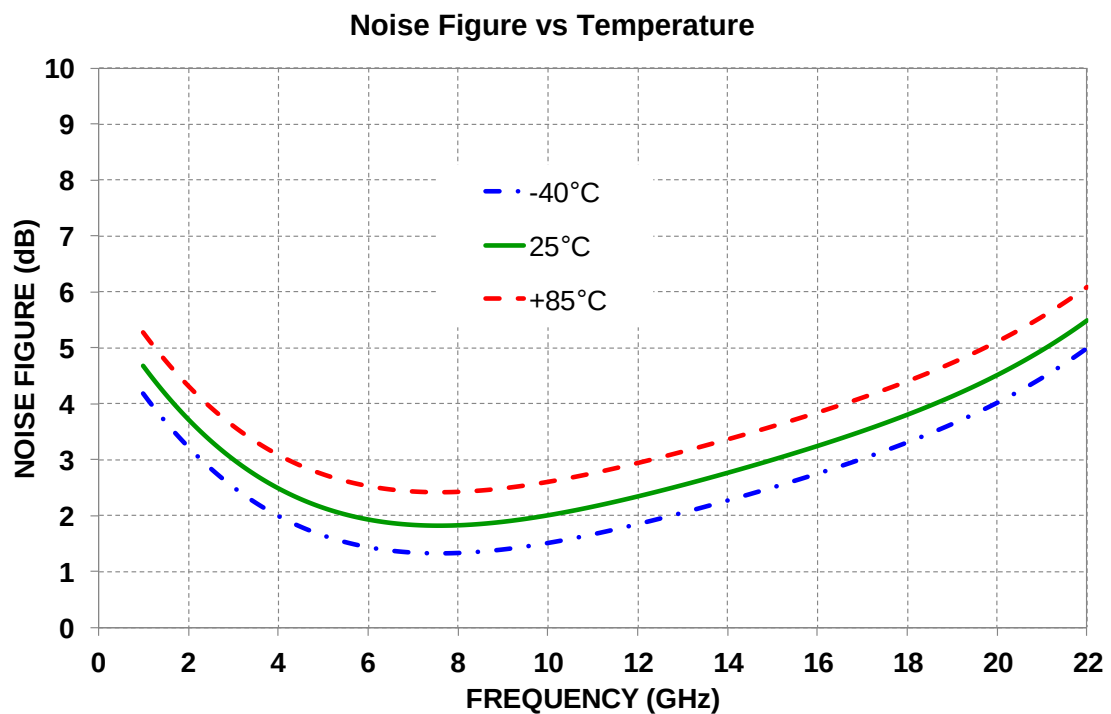
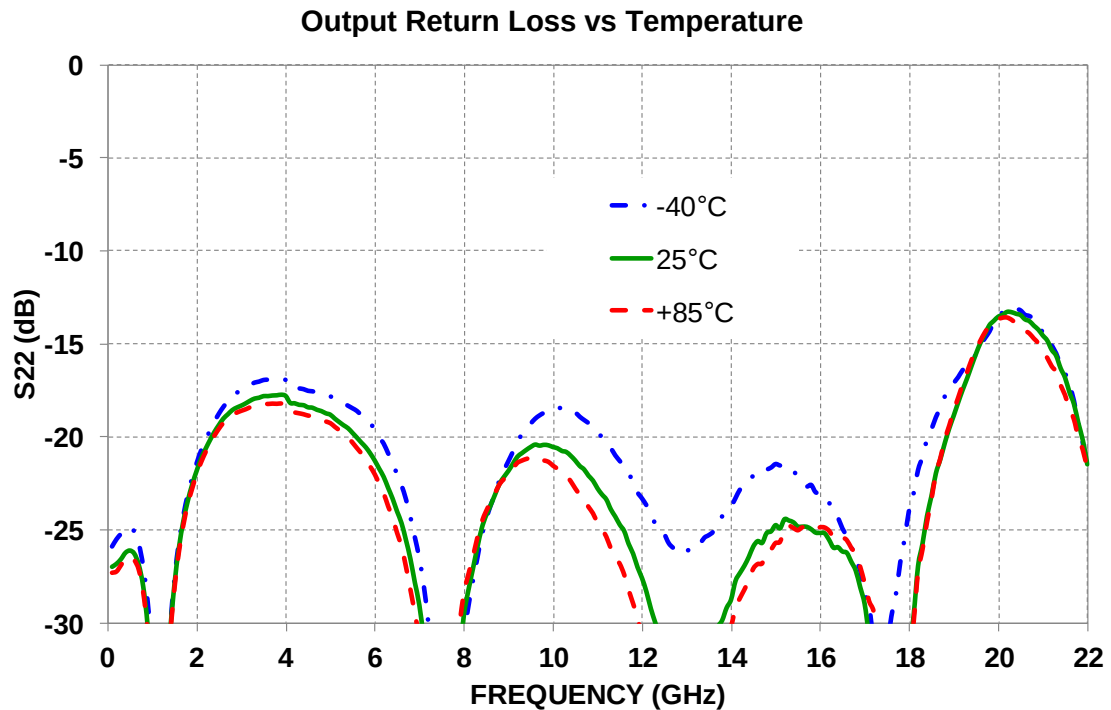
Typical Jig Measurements

T_{amb}. = +25°C, +85°C, -40°C, V_d = 7V, V_{g1} set in order to get I_{dq} = 120mA, V_{g2} = 1.5V
V_{g1} and V_{g2} remain constant versus temperature.



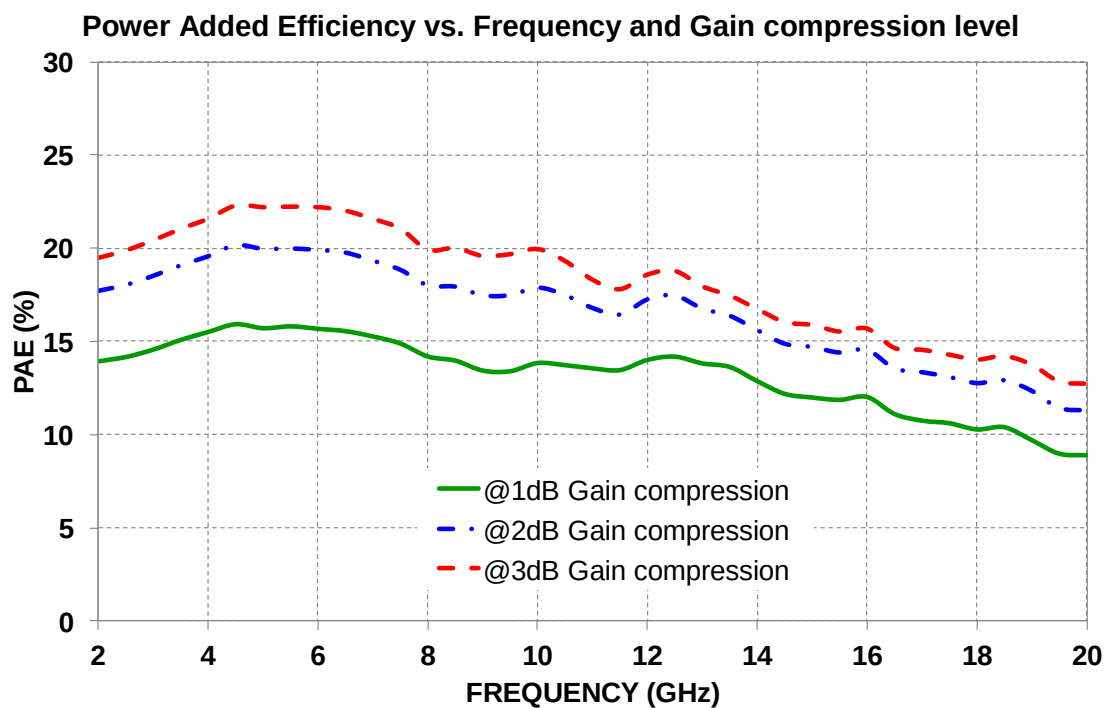
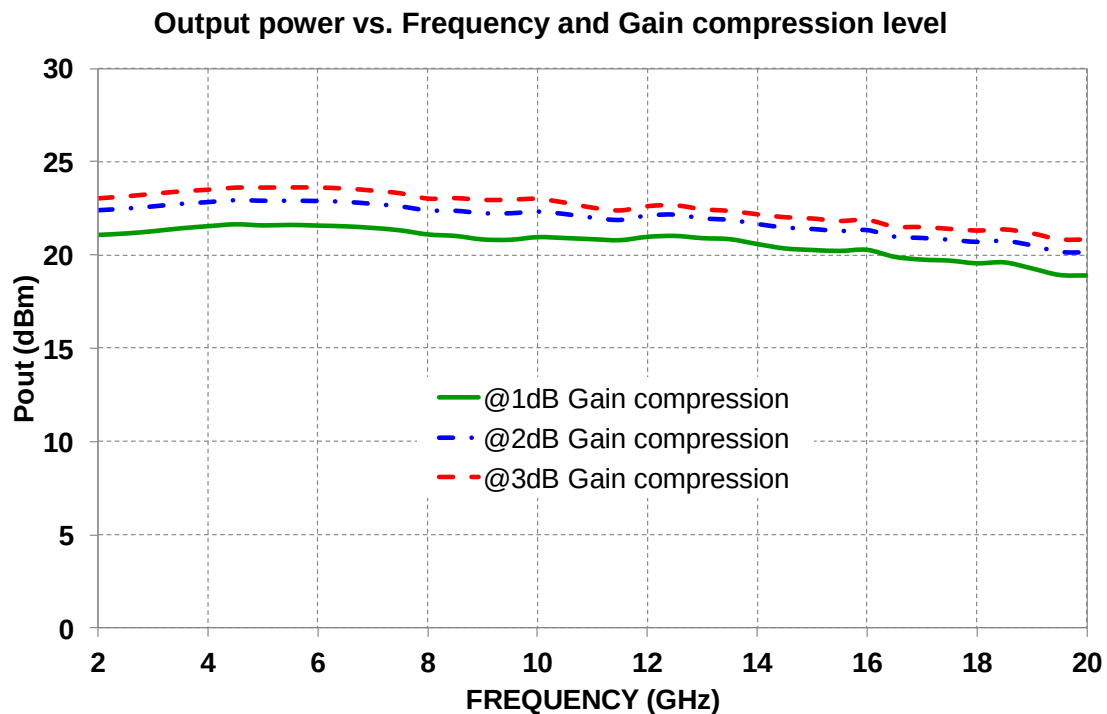
Typical Jig Measurements

Temperature.= +25°C,+85°C,-40°C, Vd =7V, Vg1 set in order to get Idq =120mA, Vg2=1.5V
Vg1 and Vg2 remain constant versus temperature.



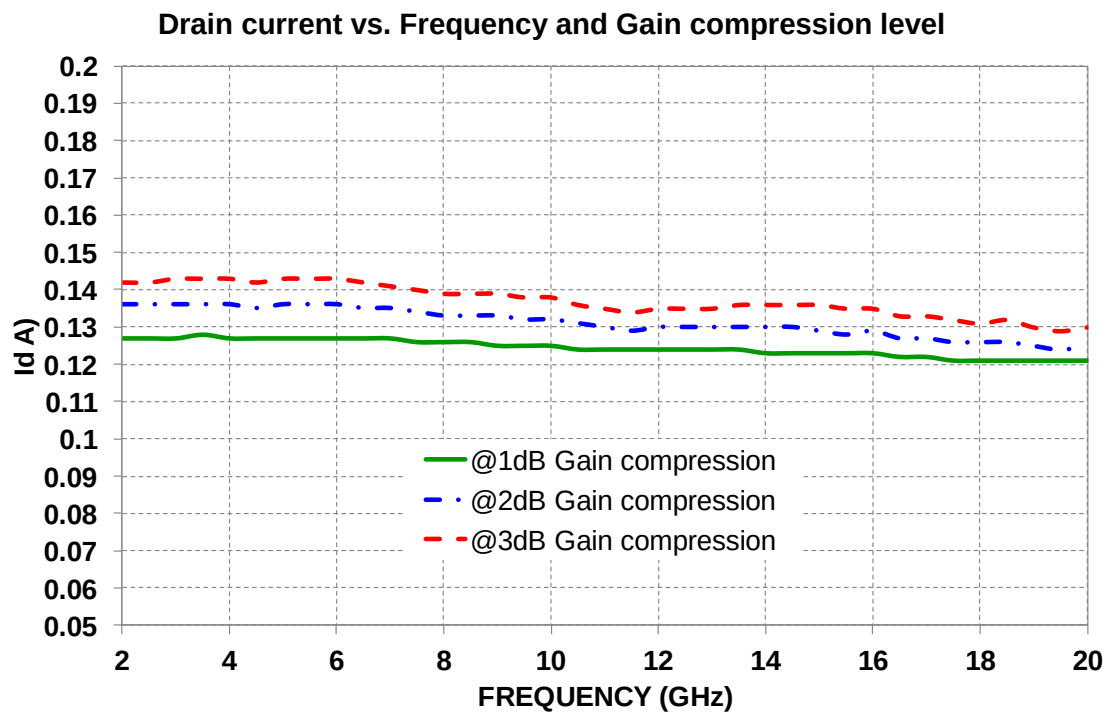
Typical Jig Measurements

Tamb= +25°C, Vd =7V, Vg1 set in order to get Idq =120mA, Vg2=1.5V



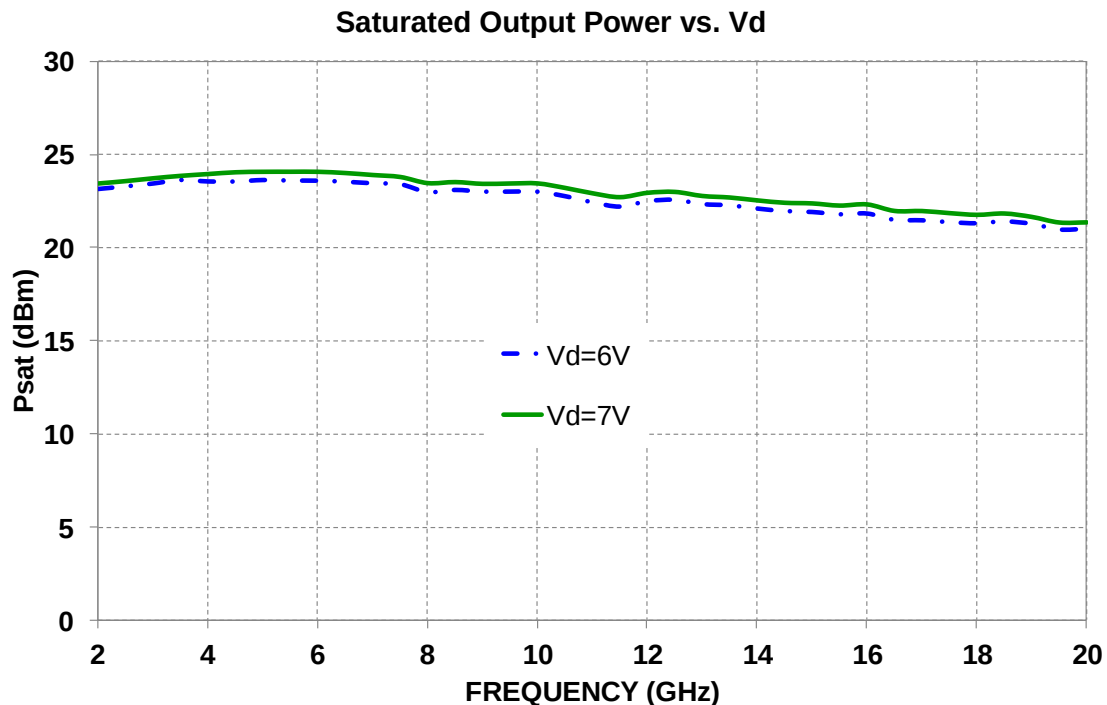
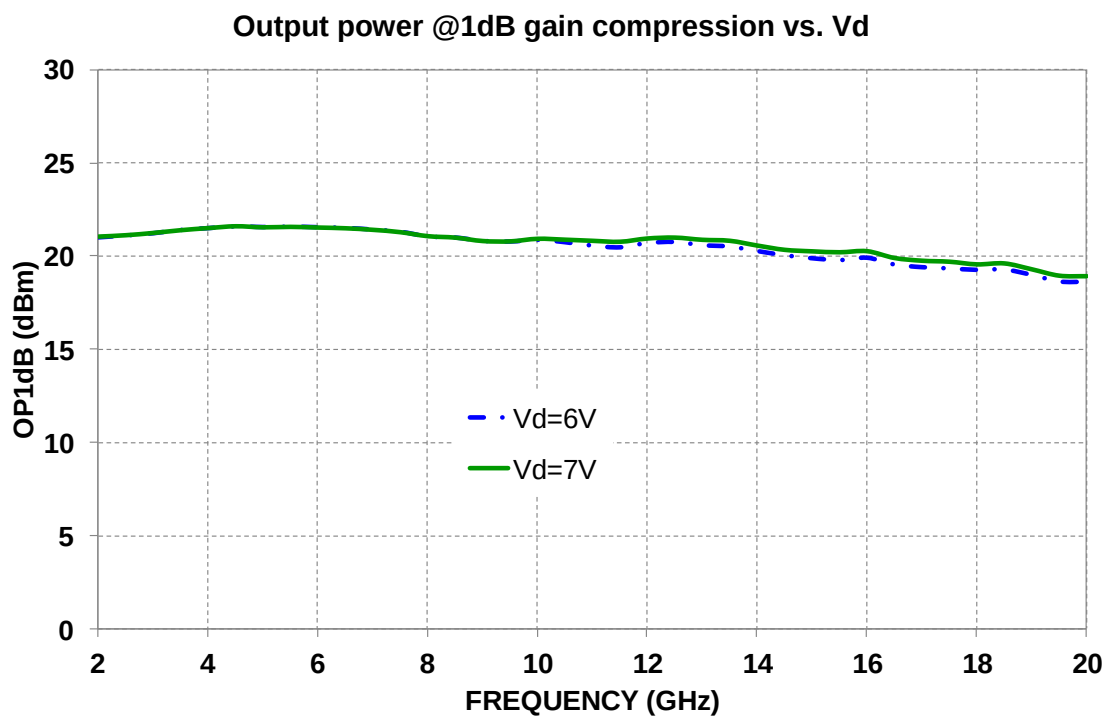
Typical Jig Measurements

Tamb.= +25°C, Vd =7V, Vg1 set in order to get Idq =120mA, Vg2=1.5V



Typical Jig Measurements

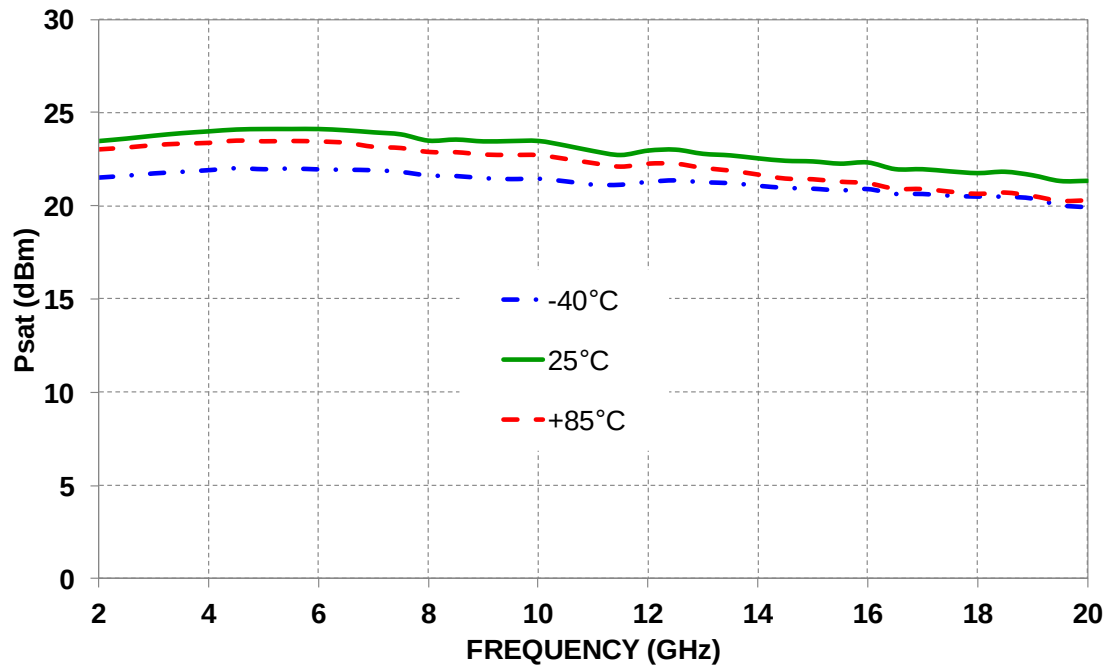
Tamb.= +25°C, Vg1 set in order to get Idq =120mA, Vg2=1.5V



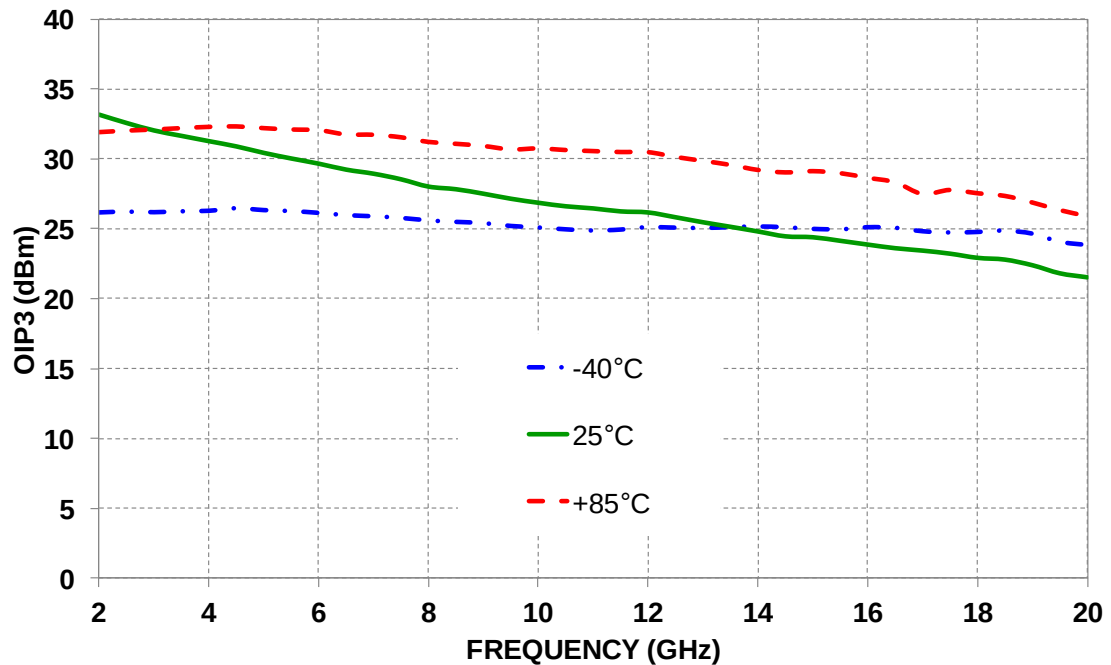
Typical Jig Measurements

Temperature.= +25°C,+85°C,-40°C, Vd =7V, Vg1 set in order to get Idq =120mA, Vg2=1.5V
Vg1 and Vg2 remain constant versus temperature.

Saturated Output power vs temperature

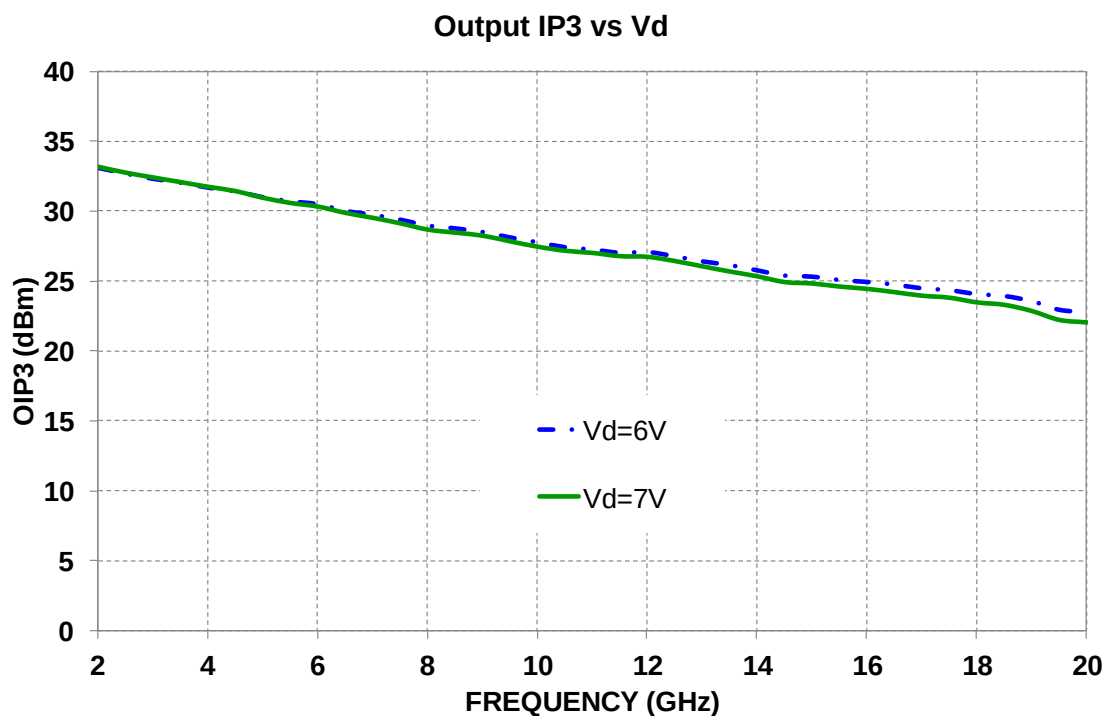


Output IP3 vs temperature

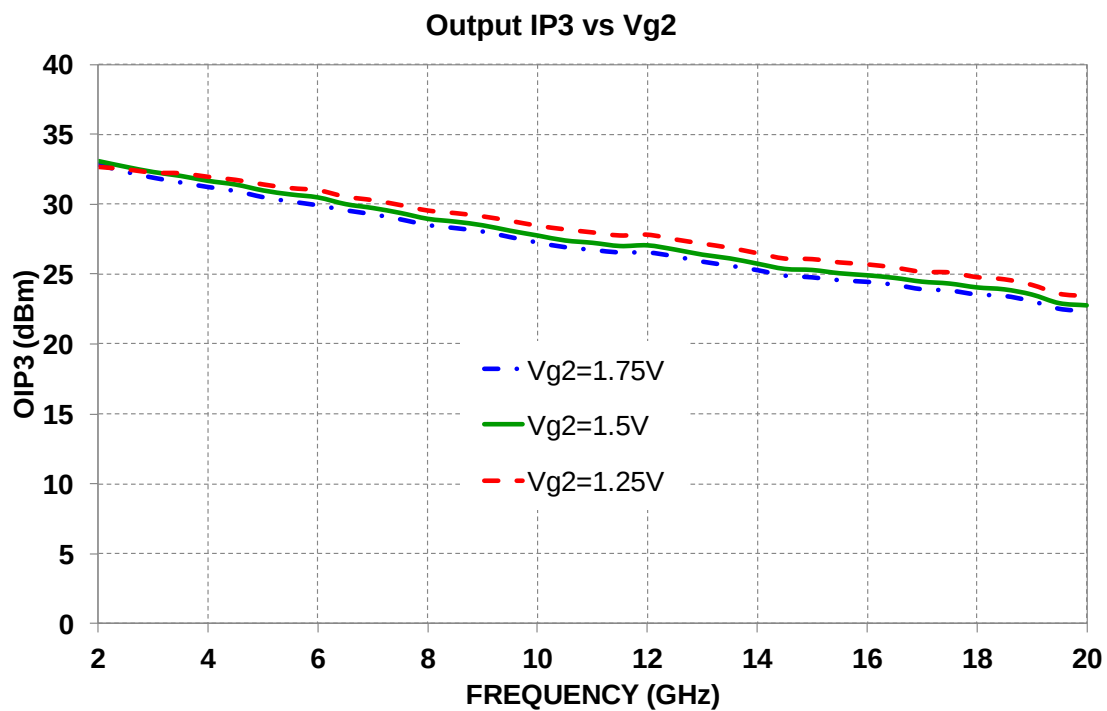


Typical Jig Measurements

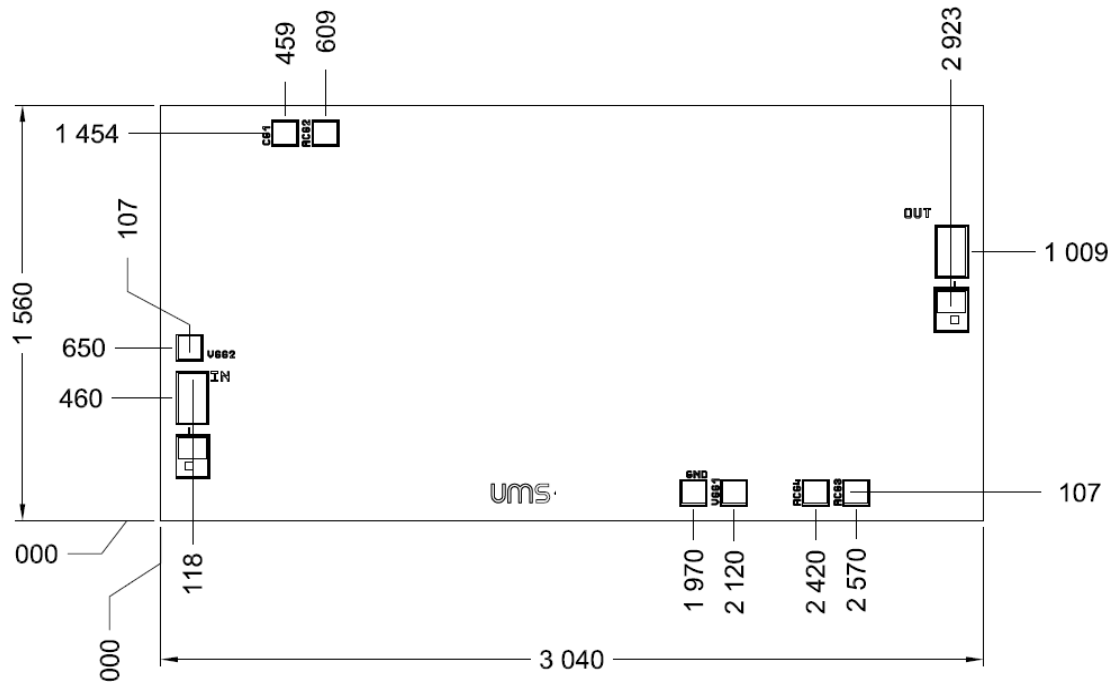
Tamb.= +25°C, Vg1 set in order to get Idq =120mA, Vg2=1.5V



Tamb.= +25°C, Vg1 set in order to get Idq =120 mA, Vd=6V



Mechanical Data: outline drawing

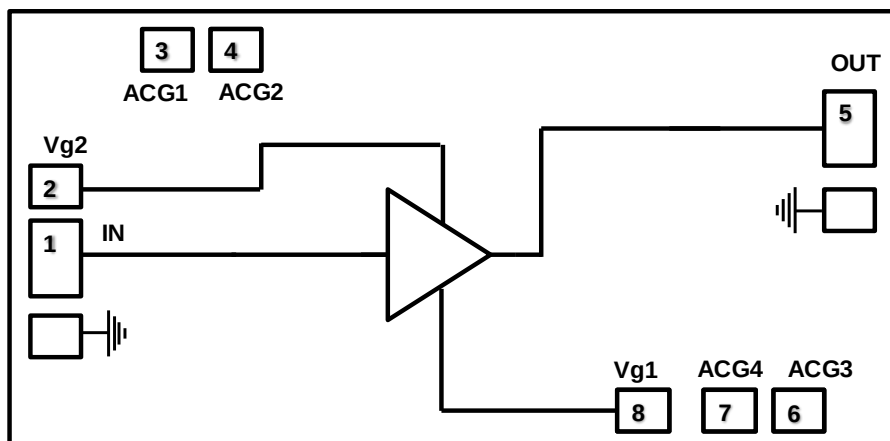


Chip width and length are given with a tolerance of $\pm 35\mu\text{m}$.

Chip thickness is 100μm.

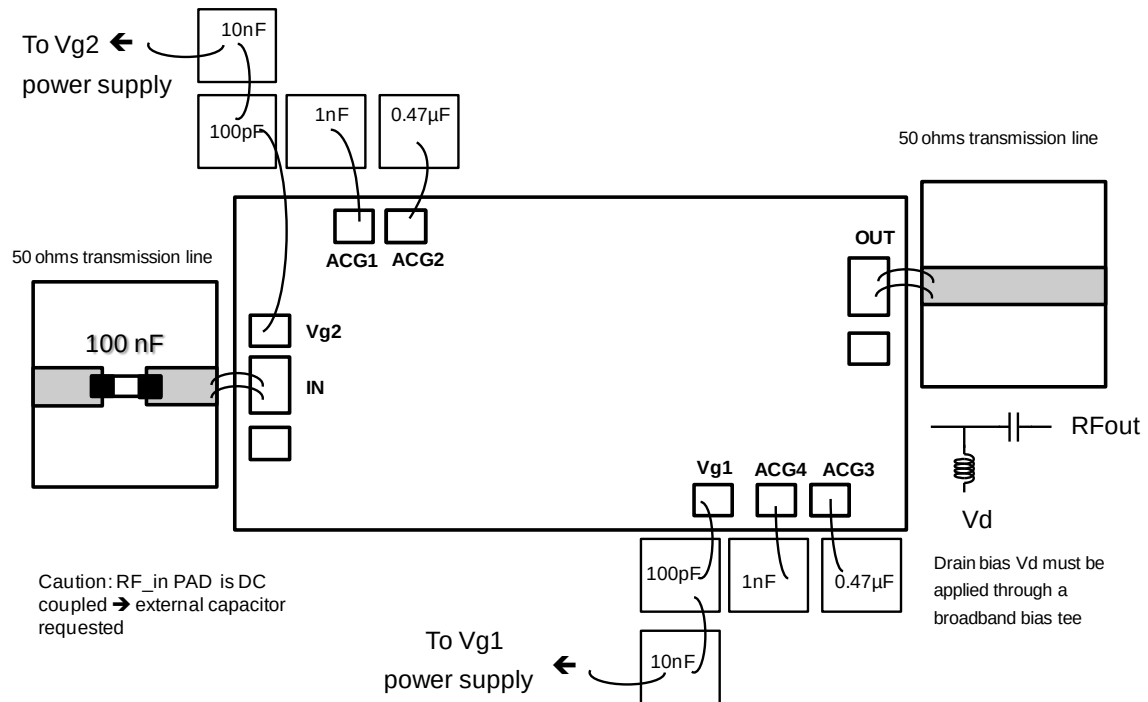
All pads are 100 μm x 100 μm , except IN and OUT pads that are 200 x 120 μm .

PAD Reference

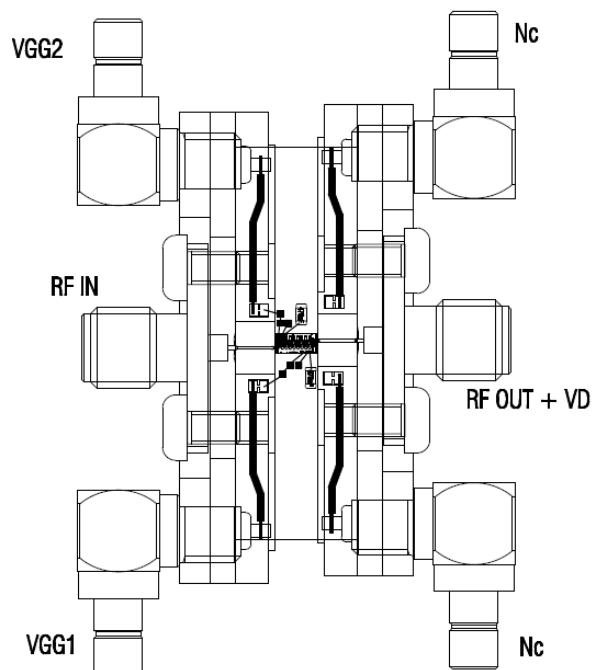


PAD Number	Name	Description
1	IN	RFIN is DC coupled and matched to 50 ohms
2	Vg2	Gate control 2 for amplifier: +1.5V should be applied for nominal operation.
3	ACG1	Low frequency termination (bypass capacitor see value next page).
4	ACG2	Low frequency termination (bypass capacitor see value next page).
5	OUT & VD	RFOUT for amplifier (matched on 50 ohms). Vd voltage should be applied on this pad through a bias Tee
6	ACG3	Low frequency termination (bypass capacitor see value next page).
7	ACG4	Low frequency termination (bypass capacitor see value next page).
8	Vg1	Gate control 2 for amplifier: about -0.2V
Die bottom	GND	Die bottom must be connected to RF/DC ground

Assembly Recommendations



Evaluation test fixture



Device Operation

Device Power Up instructions:

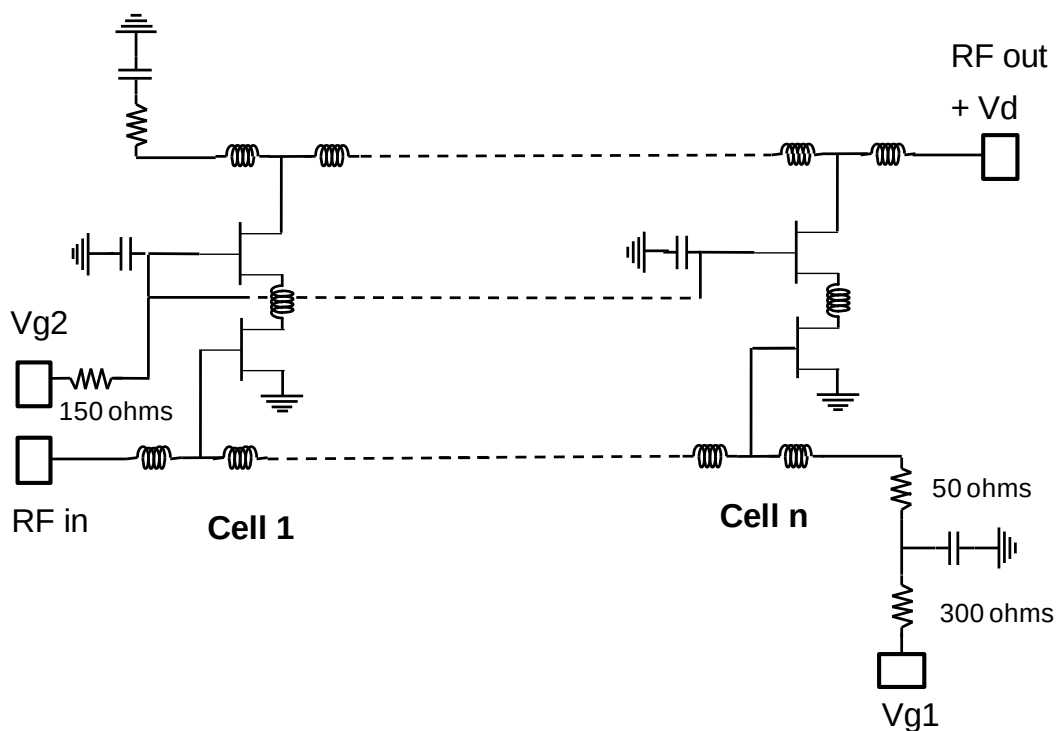
- 1) Ground the device
- 2) Set V_{g1} to -2V
- 3) Set V_{g2} to 1.5V (nominal value for V_{g2})
- 4) Set V_d to 7V (nominal value for V_d)
- 5) Set V_{g1} in the range of -0.2V for having $I_{dq}=120\text{mA}$
- 6) Apply RF input power

Device Power Down instructions:

- 1) Remove RF input power
- 2) Remove V_d
- 3) Remove V_{g2}
- 4) Remove V_{g1}

DC Schematic

$V_d=7\text{V}$, $V_{g1}=-0.2\text{V}$, $V_{g2}=1.5\text{V}$, $I_{dq}=120\text{mA}$



Notes

Recommended environmental management

UMS products are compliant with the regulation in particular with the directives RoHS N°2011/65 and REACH N°1907/2006. More environmental data are available in the application note AN0019 also available at <https://www.ums-rf.com>.

Recommended ESD management

Refer to the application note AN0020 available at <https://www.ums-rf.com> for ESD sensitivity and handling recommendations for the UMS package products.

Ordering Information

Chip form:

CHA4220-98F/00

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